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see ok

1-17-03

L. Spruell

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Robert H. Havemann	Docket No.: TI-27506
Serial No.: 10/001,472	Examiner: Wojciechowicz, E.
Filed: 11/01/01	Art Unit: 2815
For: INTEGRATED CIRCUIT HAVING A DOPED POROUS DIELECTRIC AND METHOD OF MANUFACTURING THE SAME	

Amendment under 37 CFR 1.115

Assistant Commissioner of Patents  
Washington, DC 20231

Dear Sir:

The following amendments and remarks are offered in response to the Examiner's Office Action dated 07/17/2002. They are respectfully submitted as a full and complete response to that Action.

Please amend the above-referenced application as follows:

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TECHNOLOGY CENTER 2800

In the Claims:

Cancel claims 11-20.

Please add the following claims 21-25:

21. An integrated circuit, comprising:

a semiconductor substrate;

a lowermost metal interconnect layer formed over said semiconductor substrate;

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pub. 12/17/02